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REMARKS**Listing of the Claims**

Claims 1-25 are pending as noted below. Please amend claims 6, 8, 11 and 12 as noted below.

1. (Previously presented) A stabilized cyclosiloxane material for use as a dielectric precursor, comprising a cyclosiloxane and an end-capping reagent.

2. (Previously presented) A stabilized siloxane dielectric precursor comprising a siloxane reagent dosed with a stabilizing agent(s) comprising an end-capping reagent and optionally a free radical inhibitor.

3. (Original) The stabilized siloxane dielectric precursor according to claim 1, wherein said siloxane reagent is of the formula:



wherein each of R and R' is same or different and independently selected from the group consisting of hydrogen, C₁-C₈ alkyl, C₁-C₈ alkoxy, C₁-C₈ alkene, C₁-C₈ alkyne, and C₁-C₈ carboxyl; and n is from 2 to 8.

4. (Original) The stabilized siloxane dielectric precursor according to claim 1, wherein said siloxane reagent is selected from the group consisting of: polyhedral oligomeric silsesquioxanes (POSS), octamethylcyclotetrasiloxane (OMCTS), hexamethylcyclotetra-siloxane (HMCTS), tetramethylcyclotetrasiloxane (TMCTS), and mixtures thereof.

5. (Original) The stabilized siloxane dielectric precursor according to claim 1, wherein said siloxane reagent is 1,3,5,7- tetramethylcyclotetrasiloxane (TMCTS).

6. (Currently amended) The stabilized siloxane dielectric precursor according to claim 1, wherein said stabilizing agent is present in a concentration range from about 0.01% to 10.0 % by weight, and comprises as said end-capping reagent a reagent selected from the group consisting of bis(trimethylsiloxy)methylsilane, silyl-N-methylacetamides, trifluoropropyl dimethylsilyl-N-methylacetamide and hexamethyldisilazane.

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7. (Previously presented) The stabilized siloxane dielectric precursor according to claim 1, wherein said stabilizing agent is present in a concentration range from 1.00 to 10.00 % by weight.

8. (Currently amended) The stabilized siloxane dielectric precursor according to claim 1, wherein said stabilizing agent comprises the combination of bis(trimethylsiloxy)methylsilane and butylated hydroxyl toluene.

9. (Original) The stabilized siloxane dielectric precursor according to claim 1, wherein said end-capping agent reacts with hydroxyl or radical groups resulting from cleavage of a [Si-O] bond of the siloxane dielectric precursor.

10. (Previously presented) The stabilized siloxane dielectric precursor according to claim 1, wherein said end-capping agent includes a monofunctional-silylating agent having a formula $R^1R^2R^3SiX$, wherein X is a reactive site, selected from the group consisting of H, OH, silyloxy, and nitrogen-containing silyl, each of R^1 , R^2 and R^3 is the same or different and is independently selected from hydrogen, C_1 - C_8 alkyl, and C_5 - C_{12} aryl.

11. (Currently amended) The stabilized siloxane dielectric precursor according to claim 1, wherein said end-capping reagent is selected from the group consisting of: naphthylphenylmethylsilanol (NPMS), silyl-N-methylacetamides, trifluoropropyldimethylsilyl-N-methylacetamide (TFSA), bis(trimethylsiloxy)methylsilane, and hexamethyldisilazane.

12. (Currently amended) The stabilized siloxane dielectric precursor according to claim 1, wherein said stabilizing agent further comprises a free-radical inhibitor that stops free-radical polymerization of activated siloxanes by reacting therewith.

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13. (Previously presented) The stabilized siloxane dielectric precursor according to claim 12, wherein said stabilizing agent comprises a phenol.

14. (Previously presented) The stabilized siloxane dielectric precursor according to claim 12, wherein said stabilizing agent comprises a hindered phenol.

15. (Previously presented) The stabilized siloxane dielectric precursor according to claim 12, wherein said free radical inhibitor is selected from the group consisting of butylated hydroxy toluene (BHT), hydroquinone, butylated hydro anisole (BHA) and diphenylamine.

16. (Withdrawn) A process for stabilizing a cyclosiloxane dielectric precursor, including, dosing a cyclosiloxane reagent with a stabilizing agent selected from the group consisting of end-capping reagents and optionally a free radical inhibitor.

17. (Withdrawn) The process according to claim 16, wherein said stabilizing agent is present in a concentration range from about 0.01% to 10.0 % by weight.

18. (Withdrawn) The process according to claim 16, wherein said stabilizing agent is present in a concentration range from about 0.05 to 1.00 % by weight.

19. (Withdrawn) The process according to claim 16, further comprising a purification step.

20. (Withdrawn) The process according to claim 19, wherein said dosing occurs before, after or during said purification step.

21. (Withdrawn) The process according to claim 19, wherein said purification step is selected from the group consisting of

(1) contacting the cyclosiloxane dielectric precursor with an adsorbent bed material, so as to remove therefrom at least a portion of the water, and optionally at least one other impurity,

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to produce a cyclosiloxane precursor having a reduced level of water and optionally at least one other impurity; and removing the purified cyclosiloxane precursor from the adsorbent bed material; and

(2) distilling a starting mixture comprising at least water and at least one cyclosiloxane dielectric precursor, in the presence of an azeotropic component, so as to form an azeotropic mixture with the water contained in said starting mixture; in order to produce (A) a distillate fraction comprising water and the azeotropic component and (B) a balance fraction comprising cyclosiloxane, whereby said balance fraction (B) is substantially reduced in water relative to said starting mixture; and

(3) a combination of 1 and 2;

22. (Withdrawn) The process according to claim 19, wherein said purification step reduces concentrations of water and trace acids in cyclosiloxanes to levels in a range of from about 1 to 20 ppm and from about 0.001 to 0.00001 wt %, respectively.

23. (Withdrawn) A CVD process for depositing a low dielectric constant thin film on a substrate comprising chemical vapor depositing a dielectric thin film layer on a semiconductor substrate from a cyclosiloxane reagent dosed with a stabilizing agent selected from the group consisting of end-capping reagents and optionally a free radical inhibitor.

24. (Withdrawn) The CVD process according to claim 23, further comprising:

placing the substrate in a chemical vapor deposition apparatus;

introducing at least one cyclosiloxane reagent dosed with a stabilizing agent into the apparatus;

vaporizing the cyclosiloxane reagent;

transporting the vaporized cyclosiloxane reagent into a chemical vapor deposition zone containing the substrate, optionally using a carrier gas to affect such transport;

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contacting the cyclosiloxane vapor with the substrate under chemical vapor deposition conditions to deposit a thin film comprising an organosilicon composition; and

annealing the organosilicon thin film to produce a porous, SiCOH, low dielectric constant thin film.

25. (Withdrawn) The CVD process according to claim 23, comprising residual process gases selected from the group consisting of NH_3 , O_2 and CO_2 .

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